

# 168205S-VB Datasheet

# **Dual N-Channel MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS}(V)$ $R_{DS(on)}(\Omega)$			
20	$0.024 \text{ at V}_{GS} = 4.5 \text{ V}$	6.0		
	0.028 at V <sub>GS</sub> = 2.5 V	5.0		

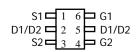
#### **FEATURES**

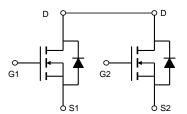
- Halogen-free Option Available
- Trench Power MOSFETs 100 %  $\rm R_{\rm g}$  Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT







<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
Continuous Drain Current (T <sub>.1</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	. I <sub>D</sub>	6.0	5.2	٨	
Continuous Diain Curient (1 j = 150 °C)	T <sub>A</sub> = 70 °C		4.8	4.2		
Pulsed Drain Current		I <sub>DM</sub>	30		А	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	1.5	1.0			
Marianum Davian Dianimaticus	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.5	1.0	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	l D	0.96	0.64		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Mariana haria ta Arkinda	t ≤ 10 s	R <sub>thJA</sub>	72	83		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	'`thJA	100	120	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	55	70		

a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$ 

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



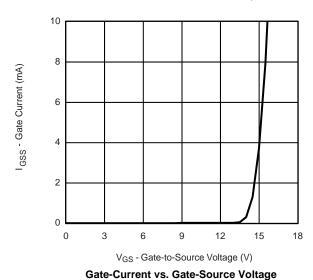
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Typ. <sup>a</sup>	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.5		1.5	V		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA		
Zara Cata Valtaga Drain Current		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C					
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α		
5 · 6 · 6 · 6 · 6 · 6	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$	0.024					
Drain-Source On-State Resistance <sup>b</sup>		$V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A}$		0.028		Ω		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 5.5 \text{ A}$		30		S		
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>S</sub> = 1.5 A, V <sub>GS</sub> = 0 V		0.71	1.2	V		
Dynamic <sup>a</sup>								
Total Gate Charge	$Q_g$			12	18			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.5 \text{ A}$		2.2		nC		
Gate-Drain Charge	$Q_{gd}$			3.6				
Turn-On Delay Time	t <sub>d(on)</sub>			245	365			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		330	495			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_G$ = 6 $\Omega$		860	1300	ns		
Fall Time	t <sub>f</sub>			510	765			

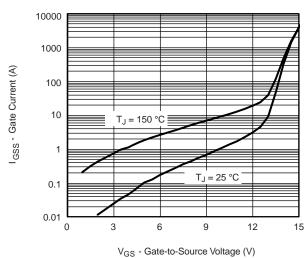
#### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

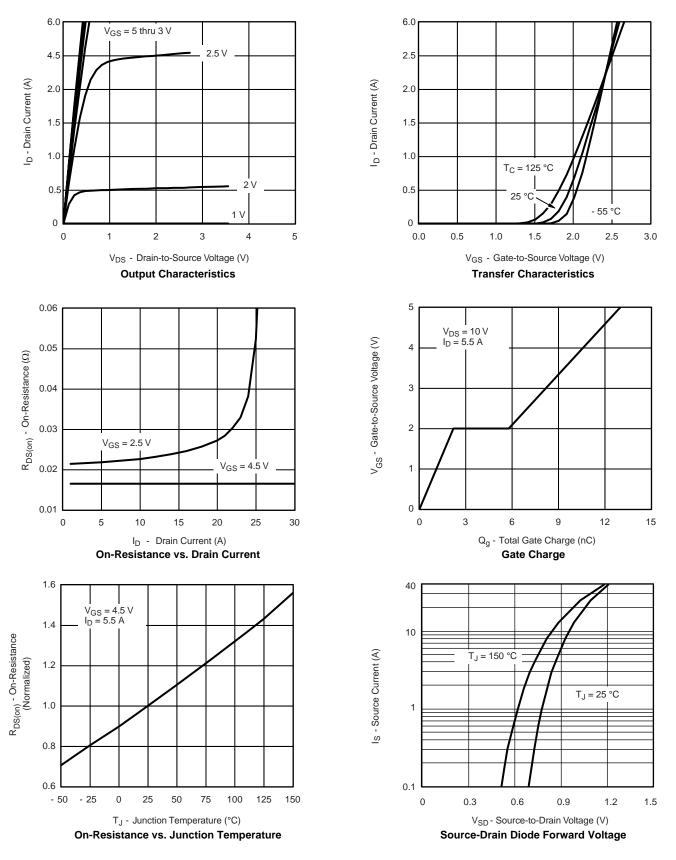




Gate Current vs. Gate-Source Voltage

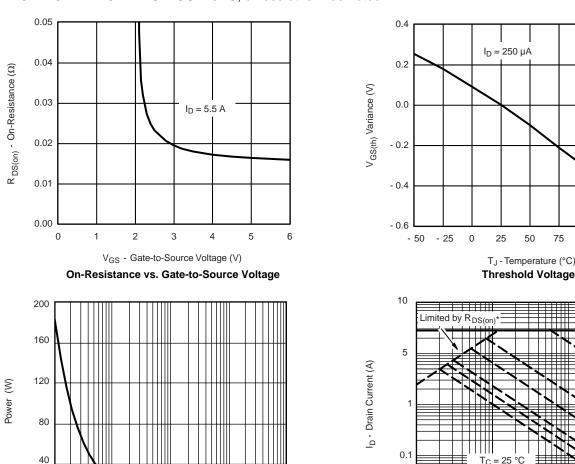


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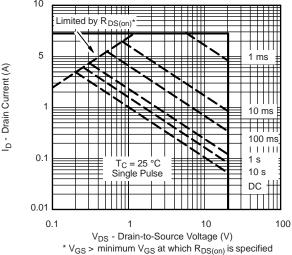


#### Time (s) Single Pulse Power

0.1

0.001

0.01

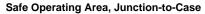


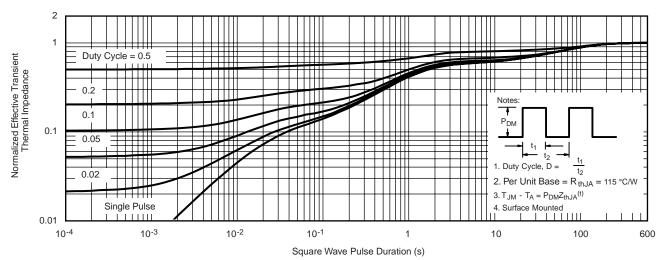
75

100

125

150

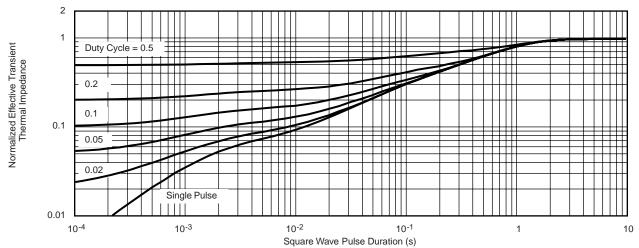




Normalized Thermal Transient Impedance, Junction-to-Ambient



# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



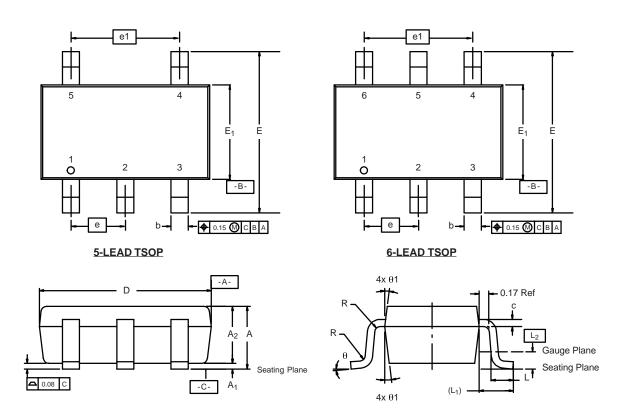
Normalized Thermal Transient Impedance, Junction-to-Foot



TSOP: 5/6-LEAD

6

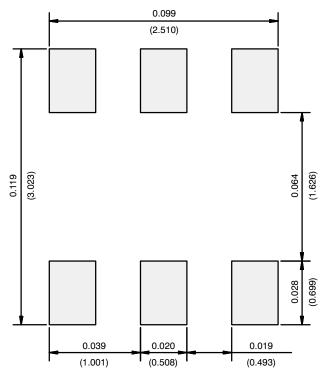
**JEDEC Part Number: MO-193C** 



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref			0.024 Ref			
L <sub>2</sub>	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
$\theta_1$	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



### **RECOMMENDED MINIMUM PADS FOR TSOP-6**



Recommended Minimum Pads Dimensions in Inches/(mm)



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